

AI  
Conte

adding a catalytic element for facilitating crystallization of an amorphous semiconductor thin film to a part or an entire region of the amorphous semiconductor thin film;  
carrying out a first heat treatment to transform the part or the entire region of the amorphous semiconductor thin film into a crystalline semiconductor thin film;  
irradiating the crystalline semiconductor thin film with ultraviolet light or infrared light; and  
carrying out a second heat treatment for the crystalline semiconductor thin film at 900 to 1200°C in an atmosphere containing hydrogen therein after the irradiating step.--

---

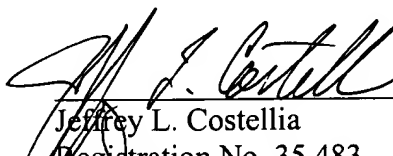
REMARKS

The Official Action mailed July 5, 2000 has been received and its contents carefully studied. Claims 1-24 are noted as pending in the Official Action.

Applicants hereby elect Group II claims - that is, claims 5-24, drawn to a method of fabricating a crystalline semiconductor thin film classified in class 438, subclass 1+. Further, Applicants add claims 25-29 herewith, which are also believed to be readable on the elected embodiment. Thus, claims 5-29 are pending and are believed to be subject to examination.

Favorable consideration is requested.

Respectfully submitted,

  
\_\_\_\_\_  
Jeffrey L. Costellia  
Registration No. 35,483  
NIXON PEABODY LLP  
8180 Greensboro Drive, Suite 800  
McLean, Virginia 22102  
(703) 790-9110

EJR/JLC/wks